Silicon NPN Power Transistors 2SC3658

DESCRIPTION

- With TO-3 package
- High voltage ,high speed
- Built-in damper diode

APPLICATIONS

- For color TV horizontal deflection output applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

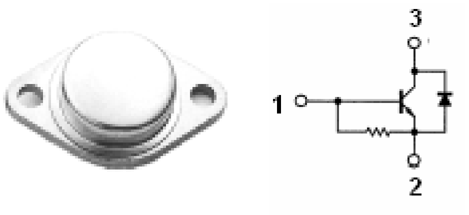

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		5	A
I_{CM}	Collector current-peak		6	A
P_C	Collector power dissipation	T_C=25℃	50	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-45~150	℃

CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CEsat}	Collector-emitter saturation voltage	I_C=5A; I_B=1.25A			2.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=5A; I_B=1.25A			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=1200V; I_E=0			0.5	mA
I_{EBO}	Emitter cut-off current	V_{EB}=6V; I_C=0			500	mA
h_{FE}	DC current gain	I_C=1A ; V_{CE}=5V	8			
V_{ECF}	Diode forward voltage	I_F=6A			2.0	V
t_f	Fall time	I_C=5A ; I_{B1}=1A;I_{B2}=-2.5A;L_B=0			0.5	μs

PACKAGE OUTLINE

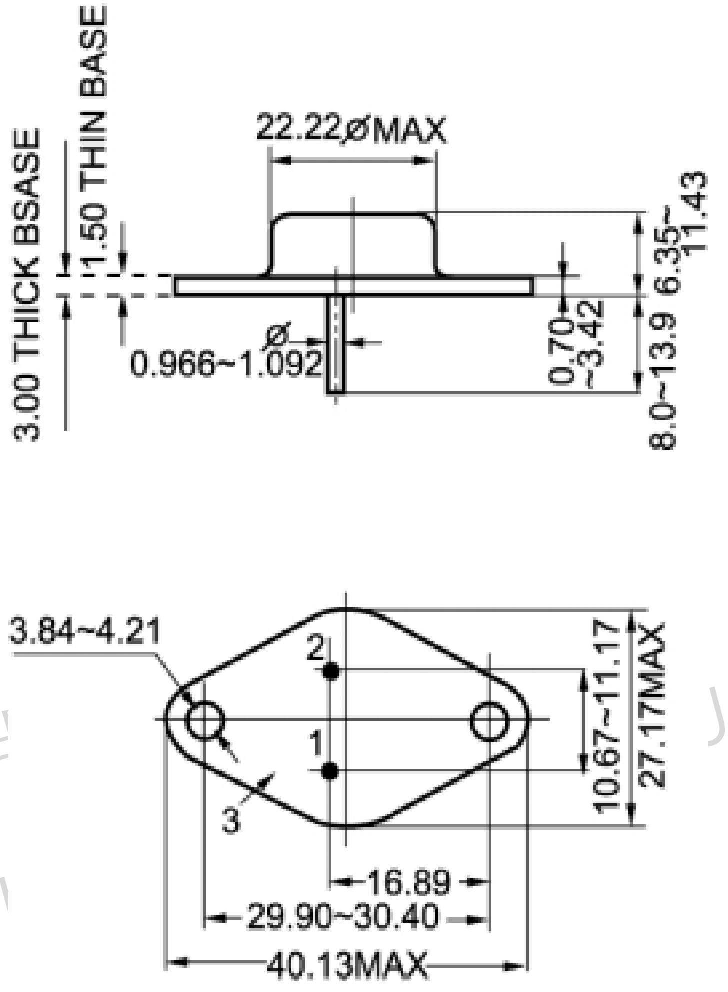

Fig.2 outline dimensions (unindicated tolerance:±0.1mm)